Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave AC control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 600 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes (Quadrants)
- Pb–Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
$\begin{array}{l} \mbox{Peak Repetitive Off-State Voltage (Note 1)} \\ (T_J = -40 \mbox{ to } +125^\circ \mbox{C}, \mbox{ Sine Wave 50 to 60 Hz}, \\ \mbox{Gate Open)} & \mbox{MAC210A8} \\ \mbox{MAC210A10} \end{array}$	V _{drm,} V _{rrm}	600 800	V
On–State RMS Current (T _C = +70°C) Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	10	A
Peak Non–Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_C = +25$ °C) Preceded and followed by rated current	I _{TSM}	100	A
Circuit Fusing Considerations, (t = 8.3 ms)	l ² t	40	A ² s
Peak Gate Power (T _C = +70°C, Pulse Width = 10 μ s)	P _{GM}	20	W
Average Gate Power $(T_C = +70^{\circ}C, t = 8.3 \text{ ms})$	P _{G(AV)}	0.35	W
Peak Gate Current (T _C = +70°C, Pulse Width = 10 μ s)	I _{GM}	2.0	A
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

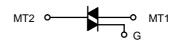
 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



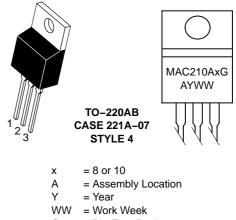
ON Semiconductor®

http://onsemi.com

TRIACS 10 AMPERES RMS 600 thru 800 VOLTS



MARKING DIAGRAM



2	= Pb-Free	Dackana
3	-10-1166	i acrage

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC210A8	TO-220AB	500 Units/Box
MAC210A8G	TO-220AB (Pb-Free)	500 Units/Box
MAC210A10	TO-220AB	500 Units/Box
MAC210A10G	TO-220AB (Pb-Free)	500 Units/Box

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

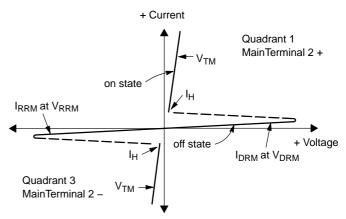
Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Case – Junction-to-Ambient	$R_{ extsf{ heta}JC} \ R_{ hetaJA}$	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

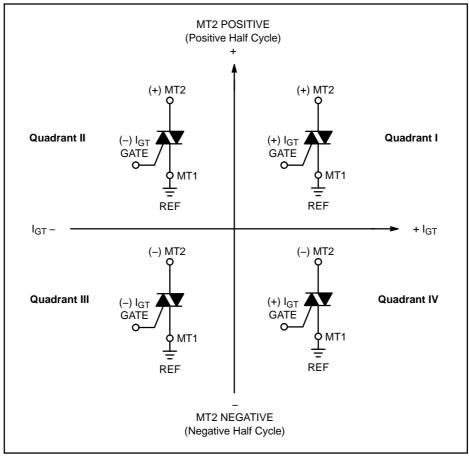
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current $(V_D = Rated V_{DRM}, V_{RRM}; Gate Open)$ $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	I _{DRM} , I _{RRM}			10 2.0	μA mA
ON CHARACTERISTICS			-		
Peak On-State Voltage (I _{TM} = \pm 14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle \leq 2%)	V _{TM}	-	1.2	1.65	V
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	I _{GT}	_ _ _ _	12 12 20 35	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V _{GT}		0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	V
Gate Non–Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, R_L = 100 Ω , T_J = +125°C) All Four Quadrants	V _{GD}	0.2	-	-	V
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = $\pm 200 \text{ mA}$, T _C = $\pm 25^{\circ}$ C)	l _Η	-	6.0	50	mA
Turn-On Time (Rated V _{DRM} , I_{TM} = 14 A) (I_{GT} = 120 mA, Rise Time = 0.1 µs, Pulse Width = 2 µs)	t _{gt}	-	1.5	-	μS
DYNAMIC CHARACTERISTICS	-		-		
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, T_C = 70°C)	dv/dt(c)	-	5.0	_	V/µs
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Voltage Rise, Gate Open, T_C = +70°C)	dv/dt	-	100	-	V/µs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

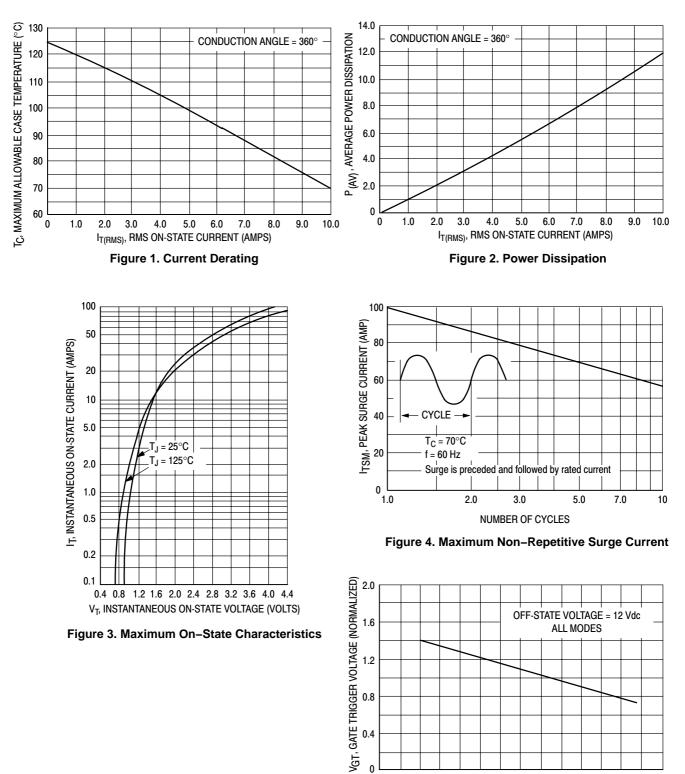


Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



T_C, CASE TEMPERATURE (°C) Figure 5. Typical Gate Trigger Voltage

20

40

60

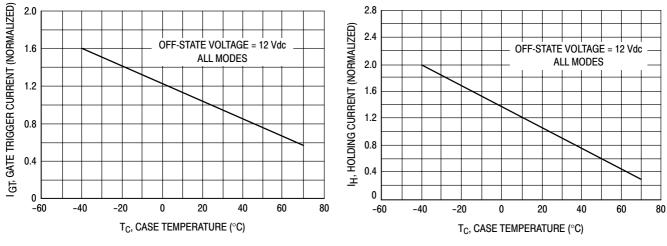
80

0

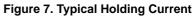
-40

-60

-20







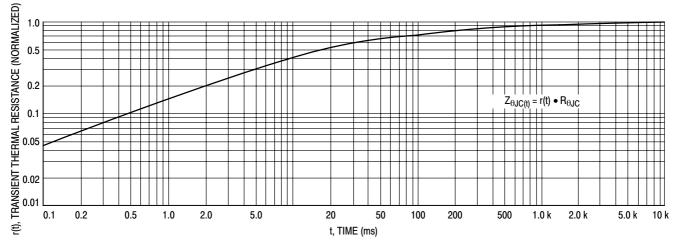
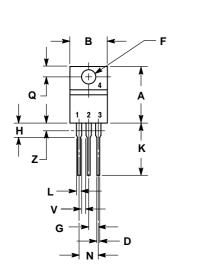
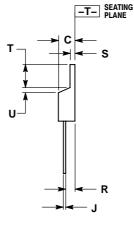


Figure 8. Thermal Response

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE AA





DIMENSION Z DEFINES A ZONE WHERE ALI BODY AND LEAD IRREGULARITIES ARE ALLOWED.				
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Z		0.080		2.04

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

STYLE 4:

NOTES:

PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2

2. MAIN TERMINAL 2 3. GATE

4. MAIN TERMINAL 2

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